

EAST - [10761488.wsp:1]

File View Edit Tools Window Help

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File: [US-PGPUB:USPAT.EPO...] [Erase]

Default operator: [OR] [Highlight all hit items initially]

1 and ((buried54 near region\$1) and tunnel near oxide)

4

BR5 form IS&S form Image Text HTML

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20050037571 A1	20050217	13	Fowler-Nordheim block alterable EEPROM memory cell	438/257		
2	<input type="checkbox"/>	<input type="checkbox"/>	US 20050029577 A1	20050210	47	Semiconductor memory device	257/315	438/211; 438/257	
3	<input type="checkbox"/>	<input type="checkbox"/>	US 20050001259 A1	20050106	14	Electrically erasable programmable read only memory (EEPROM) cells and methods of fabricating the same	257/315		
4	<input type="checkbox"/>	<input type="checkbox"/>	US 20040190339 A1	20040930	48	Semiconductor integrated circuit and nonvolatile memory element	365/185.05		
5	<input type="checkbox"/>	<input type="checkbox"/>	US 20040130947 A1	20040708	31	Flash memory with trench select gate and fabrication process	365/185.05	365/51	
6	<input type="checkbox"/>	<input type="checkbox"/>	US 20040084712 A1	20040506	12	Scaled EEPROM cell by metal-insulator-metal (MIM) coupling	257/314	257/E21.008; 257/E21.209; 257/E21.477	
7	<input type="checkbox"/>	<input type="checkbox"/>	US 20040063283 A1	20040401	46	Eeprom with split gate source side injection	438/257	257/315; 257/319; 438/264	
8	<input type="checkbox"/>	<input type="checkbox"/>	US 20040004894 A1	20040108	48	Semiconductor integrated circuit and nonvolatile memory element	365/222		
9	<input type="checkbox"/>	<input type="checkbox"/>	US 20030132478 A1	20030717	46	Multi-state operation of dual floating gate array	257/314		
10	<input type="checkbox"/>	<input type="checkbox"/>	US 20030111702 A1	20030619	46	Eeprom cell array structure with specific floating gate shape	257/438		
11	<input type="checkbox"/>	<input type="checkbox"/>	US 20030075773 A1	20030424	28	Semiconductor memory device	257/510	257/E21.682; 257/E27.103	